Unit in mm

<u>TOSHIBA</u>

TOSHIBA Photocoupler GaAłAs Ired & Photo-IC

TLP251

Inverter For Air Conditioner Induction Heating Transistor Inverter Power MOS FET Gate Drive IGBT Gate Drive

The TOSHIBA TLP251 consists of a GaAtAs light emitting diode and a integrated photodetector.

This unit is 8-lead DIP package.

TLP251 is suitable for gate driving circuit of IGBT or power MOS FET. Especially TLP251 is capable of "direct" gate drive of lower power IGBTs. (~15A)

- Input threshold current: IF=5mA(max.)
- Supply current (I_{CC}): 11mA(max.)
- Supply voltage (V_{CC}): 10–35V
- Output current (I_O): ±0.4A(max.)
- Switching time (t_{pLH} / t_{pHL}): 1µs(max.)
- Isolation voltage: 2500Vrms(min.)
- UL recognized: UL1577, file no.E67349
- Option(D4)

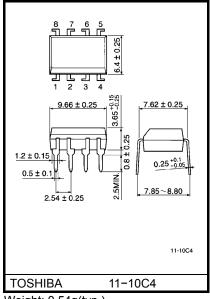
VDE Approved : DIN EN60747-5-2

Maximum Operating Insulation Voltage : 890V_{PK} Highest Permissible Over Voltage : 4000V_{PK}

(Note):When a EN60747-5-2 approved type is needed, Please designate "Option(D4)"

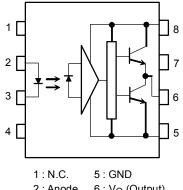
Truth Table

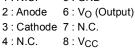
		Tr1	Tr2			
Input	On	On	Off			
LED	Off	Off	On			

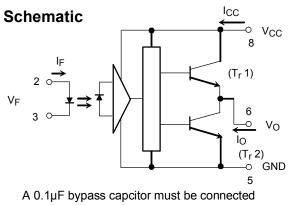


Weight: 0.54g(typ.)

Pin Configuration (top view)







between pin 8 and 5(see Note 5).

Absolute Maximum Ratings (Ta = 25°C)

	Characteristic	Symbol	Rating	Unit	
	Forward current	١ _F	20	mA	
	Forward current derating	(Ta ≥ 70°C)	ΔI _F / ΔTa	- 0.36	mA / °C
LED	Peak transient forward current	(Note 1)	I _{FPT}	1	А
	Reverse voltage		V _R	5	V
	Junction temperature	Tj	125	°C	
	"H" peak output current (P _W ≤ 2.0µs, f ≤ 15kHz)	Іорн	- 0.4	A	
	"L" peak output current (P _W ≤ 2.0μs, f ≤ 15kHz)	(Note 2)	IOPL	0.4	A
ctor	Output voltage	(Ta ≤ 70°C)	Vo	35	v
Detector		(Ta = 85°C)		24	
	Supply voltage	(Ta ≤ 70°C) (Ta = 85°C)	V _{CC}	35 24	V
	Output voltage derating (Ta ≥ 70°C)	(14 00 0)	ΔV _O / ΔTa	- 0.73	V / °C
	Supply voltage derating (Ta ≥ 70°C)		ΔV _{CC} / ΔTa	- 0.73	V / °C
	Junction temperature		Тј	125	°C
Oper	ating frequency	f	25	kHz	
Oper	ating temperature range	T _{opr} –20~85		°C	
Stora	age temperature range	T _{stg} –55~125		°C	
Lead	soldering temperature(10s)	T _{sol} 260		°C	
	Isolation voltage (AC, 1min., R.H.≤ 60%) (Note 4)			BV _S 2500	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Pulse width $P_W \le 1\mu s$, 300pps
- Note 2: Expornential waveform
- Note 3: Expornential waveform, $I_{OPH} \le -0.25A(\le 2.0\mu s)$, $I_{OPL} \le +0.25A(\le 2.0\mu s)$
- Note 4: Device considerd a two terminal device: Pins 1, 2, 3 and 4 shorted together, and pins 5, 6, 7 and 8 shorted together.
- Note 5: A ceramic capacitor(0.1µF)should be connected from pin 8 to pin 5 to stabilize the operation of the high gain linear ampifier. Failure to provide the bypassing may impair the swiching property. The total lead length between capacitor and coupler should not exceed 1cm.

Recommended Operating Conditions

Characteristic		Symbol	Min.	Тур.	Max.		Unit
Input current, on (Note6)		I _{F(ON)}	7	8	10		mA
Input voltage, off		V _{F(OFF)}	0	_	0.8		V
Supply voltage		V _{CC}	10		30	20	V
Peak output current		I _{OPH} / I _{OPL}	_		±0.1		А
Operating temperature		T _{opr}	-20	25	70	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Note 6: Input signal rise time(fall time)<0.5µs.

Electrical Characteristics (Ta = -20~70°C, unless otherwise specified)

Characteristic		Symbol	Test Cir– cuit	Test Condition		Min.	Typ.*	Max.	Unit
Input forward voltage		VF	_	I_F = 10 mA , Ta = 25°C		—	1.6	1.8	V
Temperature coefficien voltage	nt of forward	ΔV _F / ΔTa	_	I _F = 10 mA		Ι	-2.0	_	mV / °C
Input reverse current		I _R	I	V _R = 5V, Ta = 25°C				10	μΑ
Input capacitance		CT		V = 0 , f = 1MHz , Ta = 25°C			45	250	pF
Output current	"H" level	I _{OPH}	1	V _{CC} =30V	$V_{\rm CC}=30V$		-0.25	_	
	"L" level	I _{OPL}	2	(*1)	I _F =0 V ₆₋₅ = 2.5V	0.1	0.2	_	A
Output voltage	"H" level	V _{OH}	3	$V_{CC1} = +15V, V_{EE1} = -15V$ $R_L = 200\Omega, I_F = 5mA$ $V_{CC1} = +15V, V_{EE1} = -15V$ $R_L = 200\Omega, V_F = 0.8V$		11	13.2		v
	"L" level	V _{OL}	4				-14.5	-12.5	
	"H" level	Іссн	_	V _{CC} = 30V, I _F = 10mA Ta = 25°C		_	7.5	_	- mA
Currently current				V _{CC} = 30V, I _F = 10mA				11	
Supply current	"L" level	ICCL	_	V _{CC} = 30V Ta = 25°C	V _{CC} = 30V, I _F = 0mA Ta = 25°C		8	_	
				V _{CC} = 30V, I _F = 0mA			_	11	
Threshould input current	"Output $L \rightarrow H$ "	I _{FLH}	_	V_{CC1} = +15V, V_{EE1} = -15V R _L = 200Ω, V_O > 0V		_	1.2	5	mA
Threshold input voltage	"Output $H \rightarrow L$ "	V _{FHL}	_	V _{CC1} = +15V, V _{EE1} = -15V R _L = 200Ω, V _O < 0V		0.8		_	V
Supply voltage		V _{CC}				10	_	35	V
Capacitance (input–output)		Cs	_	Vs = 0 , f = 1MHz Ta = 25℃		_	1.0	2.0	pF
Resistance (input-output)		Rs	_	Vs = 500V, Ta = 25°C R.H. ≤ 60%		1×10 ¹²	10 ¹⁴	_	Ω

* All typical values are at Ta=25°C

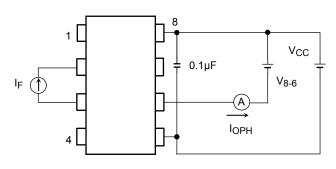
(*1): Duration of I_O time ≤ 50µs

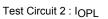
Switching Characteristics (Ta = $-20 \sim 70^{\circ}$ C, unless otherwise specified)

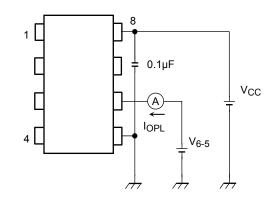
Characteristic		Symbol	Test Cir– cuit	Test Condition	Min.	Тур.*	Max.	Unit
Propagation	L→H	t _{pLH}		I _F = 8mA V _{CC1} = +15V, V _{EE1} = -15V	—	0.25	1.0	μs
delay time	H→L	t _{pHL}	5		_	0.25	1.0	
Output rise time		t _r		$R_{L} = 200 \Omega$	_	-	-	μο
Output fall time		t _f			_	-	_	
Common mode transient immunity at high level output		C _{MH}		V _{CM} = 600V, I _F = 8mA, V _{CC} = 30V, Ta = 25°C	-5000	_	_	V / µs
Common mode transient immunity at low level output		C _{ML}	6	V _{CM} = 600V, I _F = 0mA, V _{CC} = 30V, Ta = 25°C	5000			V / µs

*All typical values are at Ta= $25^{\circ}C$

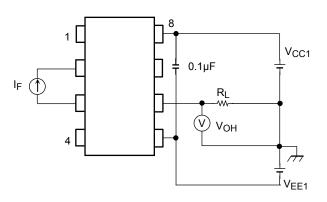
Test Circuit 1 : IOPH



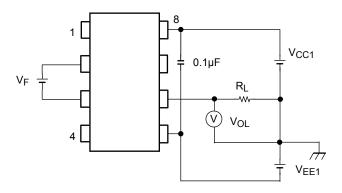




Test Circuit 3 : VOH

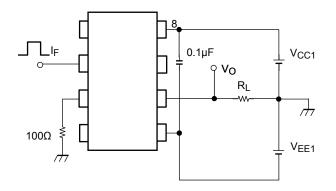


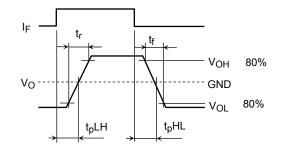
Test Circuit 4 : VOL



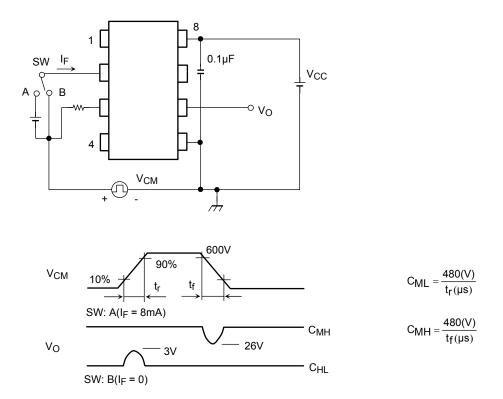
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Test Circuit 5: tpLH, tpHL, tr, tf



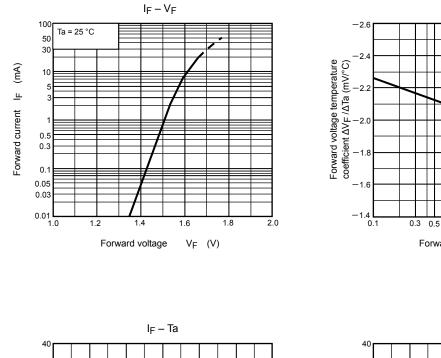


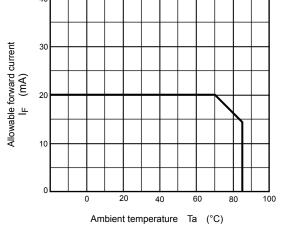
Test Circuit 6: C_{MH}, C_{ML}

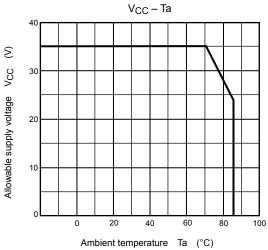


 C_{ML} (C_{MH}) is the maximum rate of rise (fall) of the common mode voltage that can be sustained with the output voltage in the low (high) state.

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 $\Delta V_F / \Delta V_F - I_F$

Ι

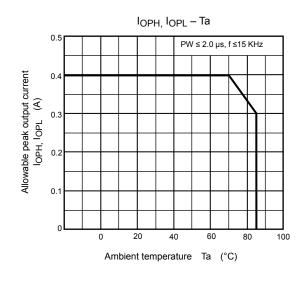
30

3 5 10

I_F (mA)

1

Forward current



RESTRICTIONS ON PRODUCT USE

20070701-EN

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